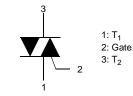


FKN08PN60S TRIAC (Silicon Bidirectional Thyristor)

Application Explanation

- Switching mode power supply, light dimmer, electric flasher unit, hair drier
- TV sets, stereo, refrigerator, washing machine
- Electric blanket, solenoid driver, small motor control
- Photo copier, electric tool





Absolute Maximum Ratings T_a = 25°C unless otherwise noted

Symbol	Parameter	Value		Rating	Units
V _{DRM} V _{RRM}	Peak Repetitive Off-State Voltage	Sine Wave 50 to 60Hz, Gate Open		600	V
I _{T (RMS)}	RMS On-State Current	Commercial frequency, sine full wave 360° conduction, Tc= 70℃		0.8	A
I _{TSM}	Surge On-State Current	Sinewave half cycle, peak value, non-repetitive	60Hz	8	A
l ² t	I ² t for Fusing	Value corresponding to halfwave, surge on-state current, tp=8.33ms		0.26	A ² s
P _{GM}	Peak Gate Power Dissipation			5	W
P _{G (AV)}	Average Gate Power Dissipation			0.1	W
V _{GM}	Peak Gate Voltage			5	V
I _{GM}	Peak Gate Current			1	А
TJ	Junction Temperature			- 40 ~ 125	°C
T _{STG}	Storage Temperature			- 40 ~ 125	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case (note1)	45	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (note2)	160	°C/W

Note1: Infinite cooling condition.

Note2: JESD51-10 (Test Borad: FR4 3.0"*4.5"*0.062", Minimum land pad)

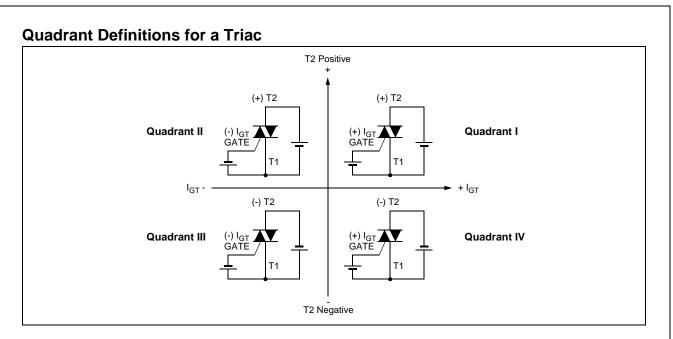
February 2008

Symbol	Parameter		Test Condition			Тур.	Max.	Units
I _{DRM} I _{RRM}	Repetieive Peak Off-State Current		V _{DRM} /V _{RRM} applied		-	-	100	μΑ
V _{TM}	On-State Voltage		T _C =25°C, I _{TM} =1.12A Instantaneous measurement		-	-	1.8	V
		I		T2(+), Gate (+)	-	-	2.0	V
V _{GT}	Gate Trigger Voltage (Note 2)	Ш	V_{D} =12V, R_{L} =100 Ω	T2(+), Gate (-)	-	-	2.0	V
		III		T2(-), Gate (-)	-	-	2.0	V
	Gate Trigger Current (Note 2)	Ι		T2(+), Gate (+)	-	-	5	mA
I _{GT}		Ш	V_{D} =12V, R _L =100 Ω	T2(+), Gate (-)	-	-	5	mA
		III		T2(-), Gate (-)	-	-	5	mA
V _{GD}	Gate Non-Trigger Voltage		T _J =125°C, V _D =1/2V _{DRM}		0.2	-	-	V
I _H	Holding Current (I, II, III)		V _D = 12V, I _{TM} = 200mA		-	-	15	mA
۱L	Latching Current	I, III	V _D = 12V, I _G = 10mA		-	-	15	mA
		Ш			-	-	20	mA
dv/dt(s)	Critical Rate of Rise of Off-State Voltag	•	V _{DRM} = 63% Rated, T _j = 125°C, Exponential Rise		20	-	-	V/µs
dv/dt(c)	Critical-Rate of Rise of Off-State Com- mutating Voltage (di/dt=-0.7A/uS)				3.0	-	-	V/µs

Electrical Characteristics T_C = 25°C unless otherwise noted

Commutation dv/dt test

V _{DRM} (V)	Test Condition	Commutating voltage and current waveforms (inductive load)
FKN08PN60S	 Junction Temperature T_J=125°C Rate of decay of on-state commutating current (di/dt)_C Peak off-state voltage V_D = 300V 	Supply Voltage Time Main Current Time Main Voltage V _D



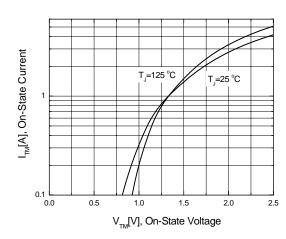
Package Marking and Ordering Information

Device Marking	Device	Package	Packing	Tape Width	Quantity
K08PN60S	FKN08PN60S	TO-92	BULK		

Typical Performance Characteristics

Figure 1. On-State Characteristics





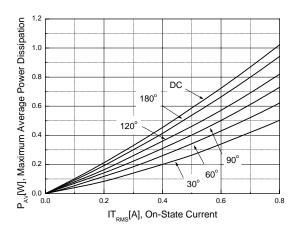
60°

90

0.6

0.7

0.8





Maximum Allowable Case Temperature, $T_{\rm c} {\rm [}^{\circ} {\rm C} {\rm]}$

120

110

100

90

80

70

0.0

0.1

0.2

Figure 4. Typical Gate Trigger Current vs Junction Temperature

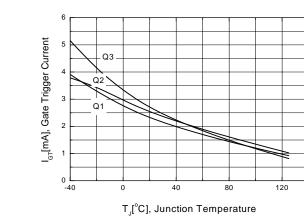


Figure6. Typical Latching Currrent vs Junction Temperature

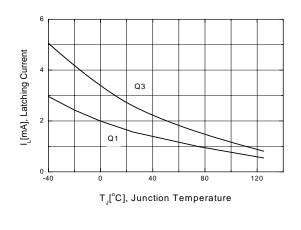


Figure5. Typical Gate Voltage vs Junction Temperarure

120°

180°

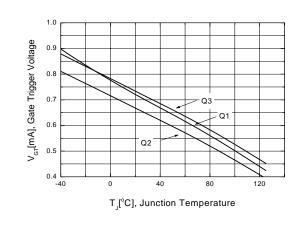
0.3

DC

0.4

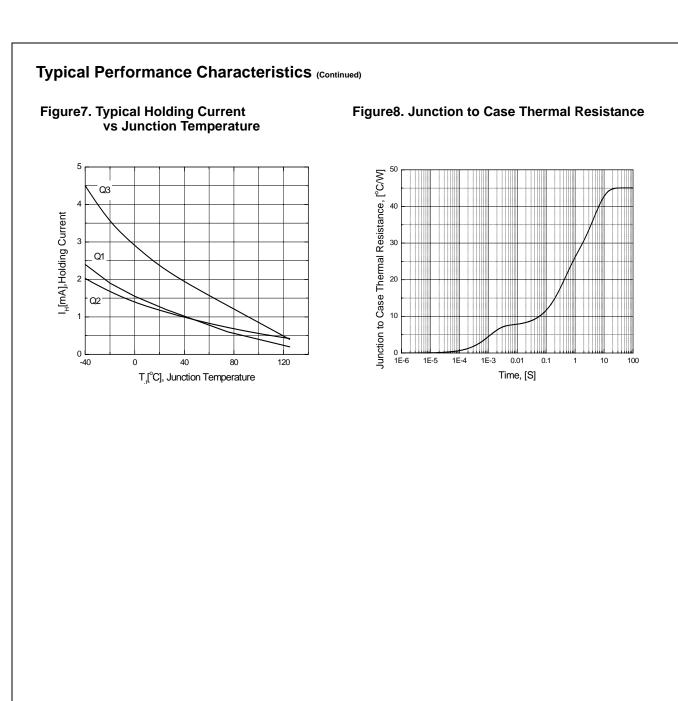
IT_{RMS}[A], On-State Current

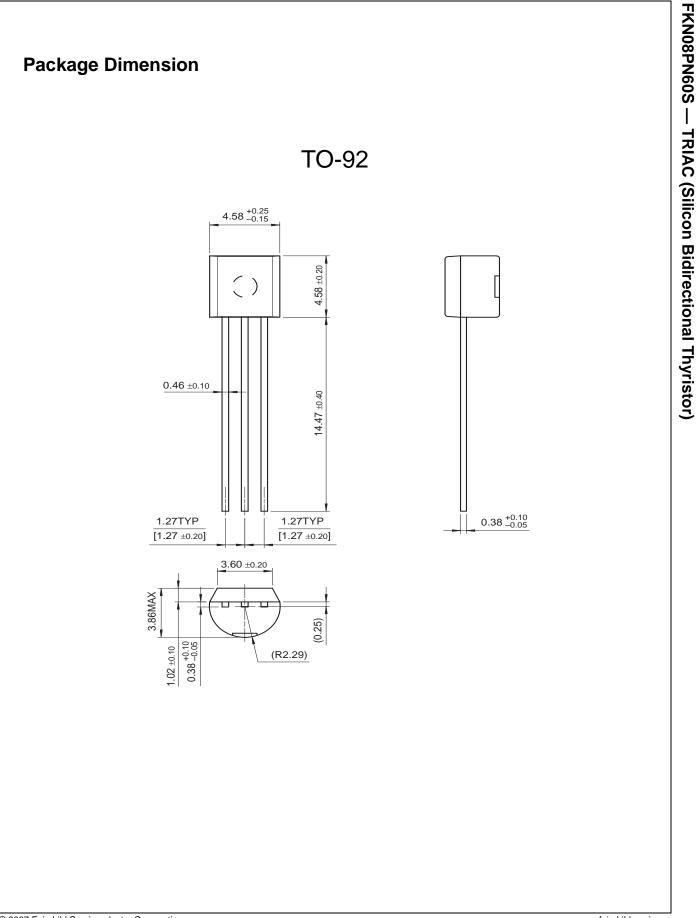
0.5



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